

(1) IPD: Industrial & Power Discretes - ASD: Application Specific Device – IPAD™: Integrated Passive and Active Devices

PCN Product/Process Change Notification

Additionnal Assembly site in China for Rectifiers housed in TO 247 package

Notification number:	IPG-DIS/15/9111	Issue Date	20/02/2015
Issued by	Aline AUGIS		
Product series affected by the change		STTH50W03CW STTH6003CW STTH60RL03CW STTH60W03CW	
Type of change		Multisourcing assembly site	

Description of the change

New manufacturing location for TO247:

Back-end			Back-end					
	Name	Туре	Country	Marking	Name	Туре	Country	Marking
TO247	LGG ST (ST Chin	China	<u> </u>	Subco	subco	China	GF
Rectifier	199	51	Cillia	G4	STS	ST	China	GK

Reason for change

Following the continuous improvement of our service and in order to increase our capacity this document is announcing that the products housed in TO247, listed in this PCN, will be manufactured in Subcontractor plant (China) and in ST assembly site in Shenzhen plant.

Former versus changed product:	The changed products do not present modified electrical, dimensional or thermal parameters, leaving unchanged the current information published in the product datasheet
	There is no change in the packing modes and the standard delivery quantities either.
	The products remain in full compliance with the ST ECOPACK®2 grade ("halogen-free").
Disposition of former products	

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Deliveries of former product we 'll continue as long as products stocks last

STMicroelectronics IPD - ASD & IPAD[™] Division¹ BU Rectifiers



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Marking and traceability

Traceability for the implemented change will be ensured by the marking, an internal codification and by the Q.A. number. "GF and GK" marked on the package and box label.

Qualification complete date	15-02-2015
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Forecasted sample availability

Product family	Sub-family	Commercial part Number	Availability date
BIPOLAR RECTIFIER	TO247	STTH50W03CW	NOW
BIPOLAR RECTIFIER	TO247	STTH6003CW	NOW
BIPOLAR RECTIFIER	TO247	STTH60RL03CW	NOW
BIPOLAR RECTIFIER	TO247	STTH60W03CW	NOW

Change implementation schedule

Sales types	Estimated production start	Estimated first shipments				
STTH50W03CW STTH6003CW STTH60RL03CW STTH60W03CW	W15-2015	W21-2015				
Comments:						
Customer's feedback						
Please contact your local ST sales representative or quality contact for requests concerning this change notification.						
Absence of acknowledgement of this PCN within 30 days of receipt will constitute acceptance of the change Absence of additional response within 90 days of receipt of this PCN will constitute acceptance of the change						

Qualification program and results	QRP15002 Attached
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ST Restricted

IPG (Industrial and Power Group) ASD & IPAD division Quality and Reliability

Reliability Evaluation Report

Additional Chinese subcontractor qualification TO247 and MAX247 packages for Rectifiers products

General Info	ormation
Product Description	Rectifier
Product scope	STTH50W03CW STTH6003CW STTH60RL03CW STTH60W03CW STPS80H100CY STPS80L60CY STTH8003CY
Product Group	ASD&IPAD
Product division	IPG
Package	TO247 MAX TO247
Maturity level step	QUALIFIED

Locations					
	ST TOURS (France)				
Wafer fab	ST ANG MO KIO				
	(SINGAPORE)				
Assembly plant	SUBCONTRACTOR (CHINA)				
Reliability Lab	ST TOURS (FRANCE)				
Reliab	ility Assessment				
	PASS				

DOCUMENT INFORMATION

Version	Date	Pages	Prepared by	Approved by	Comment
1.0	02/02/2015		Aude DROMEL	Jean-Paul REBRASSE	

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

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1 APPLICABLE AND REFERENCE DOCUMENTS

Document reference	Short description
JESD 47	Stress-Test-Driven Qualification of Integrated Circuits
JESD 94	Application specific qualification using knowledge based test methodology
JESD 22	Reliability test methods for packaged devices

2 GLOSSARY

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SS	Sample Size	
PC	Pre-conditioning	
HTRB	High Temperature Reverse Bias	
HTFB	High Temperature Forward Bias	
тс	Temperature Cycling	
PCT / AC	Pressure Pot 2 bars / Autoclave	
THB / HTRB	Thermal Humidity Bias / High Temperature Reverse Bias	
UHAST	Unbiased Highly Accelerated Stress Test	
IOLT / TF	Intermittent Operational Life Test / Thermal Fatigue	
DPA	Destructive Physical Analysis	
RSH	Resistance to Solder Heat	
SD	Solderability	
GD	Generic Data	

<u>3 RELIABILITY EVALUATION OVERVIEW</u>

3.1 **Objectives**

The objective is to qualify new assembly subcontractor for TO247 and TO247 MAX packaging for Rectifiers in order to improve the quality of service.

Product perimeter is composed of:

- STTH50W03CW
- STTH6003CW
- STTH60RL03CW
- STTH60W03CW
- STPS80H100CY
- STPS80L60CY
- STTH8003CY

The reliability test methodology used follows the JESD47-H: « Stress Test Driven Qualification Methodology » and is package oriented.

The following reliability tests are:

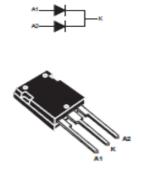
- TC to ensure the mechanical robustness of the products.
- THB and Autoclave to check the robustness to corrosion and the good package hermeticity.
- RSH and Solderability test to check package robustness against customer assembly on board.

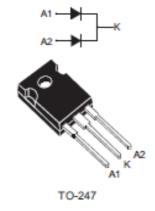
3.2 **Conclusion**

Qualification Plan requirements have been fulfilled without exception. Reliability tests have shown that the devices behave correctly against environmental tests (no failure). Moreover, the stability of electrical parameters during the accelerated tests demonstrates the robustness of the products and safe operation, which is consequently expected during their lifetime.

4 DEVICE CHARACTERISTICS

4.1 Device description





Max247

4.2 Construction note

	STTH50W03CW, STTH6003CW, STTH60RL03CW, STTH60W03CW			
Wafer/Die fab. information				
Wafer fab manufacturing location	ST TOURS FRANCE			
Technology / Process family	BIPOLAR RECTIFIER			
Wafer Testing (EWS) information				
Electrical testing manufacturing location	ST TOURS FRANCE			
Assembly information				
Assembly site	SUBCONTRACTOR – CHINA			
Package description	TO 247			
Molding compound	ECOPACK®2 ("Halogen-free") molding compound			
Lead finishing material	Leadfree (100% pure Tin)			
Final testing information				
Testing location	SUBCONTRACTOR – CHINA			

	STPS80H100CY, STPS80L60CY, STTH8003CY				
Wafer/Die fab. information					
Wafer fab manufacturing location	ST ANG MO KIO (SINGAPORE)				
Technology / Process family	POWER SCHOTTKY				
Wafer Testing (EWS) information					
Electrical testing manufacturing location	ST ANG MO KIO (SINGAPORE)				
Assembly information					
Assembly site	SUBCONTRACTOR – CHINA				
Package description	TO 247 MAX				
Molding compound	ECOPACK®2 ("Halogen-free") molding compound				
Lead finishing material	Leadfree (100% pure Tin)				
Final testing information					
Testing location	SUBCONTRACTOR – CHINA				

5 TESTS RESULTS SUMMARY

5.1 Test vehicles

Lot #	Part Number	Package	Comments
Lot 1	STTH50W03CW	TO247	
Lot 2	STTH6003CW	TO247	
Lot 3	STPS80L60CY	TO247 MAX	
Lot 4	STPS80H100CY	TO247 MAX	
GD1	STPS80170CW	TO247	Similar package
GD2	STTH3002CW	TO247	Similar package

Detailed results in below chapter will refer to P/N and Lot #.

5.2 Test plan and results summary

Test PC Std ref.		Std rof	Conditions	SS	Steps	Failure/SS					
Test	Test PC Staret.	Lot 1				Lot 2	Lot 3	Lot 4	GD1	GD2	
								-			
HTRB	Ν	JESD22 A-108	V = 80% VRRM Tj = 150°C	154	1000h					0/77	0/77
Packa	ge O	riented To	ests								
тс	Ν	JESD22 A-104	Frequency (cy/h)=2cy/h Temperature (high)=150°C Temperature (low)=-65°C	75	500cy	0/25	0/25	0/25			
RSH	N	JESD22 B-106-A	Dippings=2 Temperature=260°C Time (off)=15s Time (on)=10s	60	MESURE		0/30	0/30			
тнв	Ν	JESD22 A-101	Humidity (HR)=85% Temperature=85°C Tension=80% VRRRM, max 100V	75	1000h	0/25	0/25		0/25		
РСТ	Ν	JESD22 A-102	Pressure=2.05bar Temperature=121°C 75 96h		96h	0/25	0/25		0/25		
SD	N	STWet ageinginternalSnPn bath bath 245°C300018688SnAgCu bath 245°C		N/A				0/30			



<u>6 ANNEXES</u>

6.1 **Tests Description**

Test name Standard Reference			Description	Purpose			
Die Oriented							
tryi HTRB follo High Temperature low Reverse Bias max diff		trying follov low p max. diffus	device is stressed in static configu g to satisfy as much as possib wing conditions: oower dissipation; supply voltage compatible sion process and internal c ations	ble the accelerated way. To maximize the electrical field across either reverse- biased junctions or dielectric layers, in order to investigate the failure modes linked to mobile			
			Package	Oriented			
RSH Resistance to solder heat	JESD22 B- 106-A		Device is submitted to a dipping in a solder bath at 260°C with a dwell time of 10s. Only for through hole mounted devices.	This test is used to determine whether solid state devices can withstand the effects of the temperature to which they will be subjected during soldering of their leads. The heat is conducted through the leads into the device package from solder heat at the reverse side of the board. This procedure does not simulate wave soldering or reflow heat exposure on the same side of the board as the package body.			
TC Temperature Cycling	emperature JESD22 A-		The device is submitted to cycled temperature excursions, between a hot and a cold chamber in air atmosphere	To investigate failure modes related to the thermo- mechanical stress induced by the different thermal expansion of the materials interacting in the die-package system. Typical failure modes are linked to metal displacement, dielectric cracking, molding compound delamination, wire-bonds failure, die-attach layer degradation.			
THB Temperature Humidity Bias	perature JESD22 A- internal power dissipation, and		configuration minimizing its internal power dissipation, and stored at controlled conditions of ambient temperature and	To evaluate the package moisture resistance with electrical field applied, both electrolytic and galvanic corrosion are p			
PCT Pressure Cooker Test	JESD2 102		The device is stored in saturated steam, at fixed and controlled conditions of pressure and temperature.	To investigate corrosion phenomena affecting die or package materials, related to chemical contamination and package hermeticity.			